File   View   Edit   Tools   Window   Help

BRS: ferromagnetic and offsett
BRS: 1 2
BRS:
BRS:
BRS: upside

⊘ Pending
Active
  L2: (64) nitride adj memory
  L1: (382) NROM
  L3: (285) 1 and nitride
  L4: (47278) bit adj line
  L5: (175) 3 and 4
Failed
  (0) AND adj logic

DBs: USPAT, US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
Default operator: OR

3 and 4

	U	1	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	Retrieval Clu	Inventor	S	C	P		3	Image
1			US 20030185071 A1	20031002	24	Nonvolatile semiconductor memory device and method of manufacturing	365/200			Yoshino, Akira	✓					US 2003
2	✓		US 20030185053 A1	20031002	16	Fast program to program verify method	365/185.18			Ogura, Seiki et al.						US 2003
3	✓		US 20030174570 A1	20030918	43	Semiconductor memory device having potential control circuit	365/230.03			Ooishi, Tsukasa						US 2003
4	✓		US 20030161183 A1	20030828	120	Digital multilevel non-volatile memory system	365/185.03	365/185.2		Tran, Hieu Van						US 2003
5	✓		US 20030157758 A1	20030821	73	Non-volatile semiconductor memory device and manufacturing method the	438/199			Ohtani, Jun et al.						US 2003
6			US 20030155607 A1	20030821	87	SEMICONDUCTOR INTEGRATED CIRCUIT	257/324			Kamigaki, Yoshiaki et al.	✓					US 2003
7			US 20030151946 A1	20030814	46	Nonvolatile semiconductor memory device having control circuit	365/185.03			Ooishi, Tsukasa	✓					US 2003
8	✓		US 20030145176 A1	20030731	28	Mass storage device architecture and operation	711/154	711/104; 711/162		Dvir, Ran et al.						US 2003
9	✓		US 20030142544 A1	20030731	24	Mass storage array and methods for operation thereof	365/185.16			Maayan, Eduardo et al.						US 2003
10	✓		US 20030141532 A1	20030731	23	Non-volatile semiconductor memory device of which bit line withstand volt	257/304			Kato, Hiroshi						US 2003
11	✓		US 20030134478 A1	20030717	10	Non-volatile memory and fabrication thereof	438/275	438/278; 438/291		Lai, Han-Chao et al.						US 2003
12	✓		US 20030134476 A1	20030717	9	Oxide-nitride-oxide structure	438/261			Roizin, Yakov et al.						US 2003
13	✓		US 20030132488 A1	20030717	10	Non-volatile memory and fabrication thereof	257/390	257/391		Lai, Han-Chao et al.						US 2003
14	✓		US 20030128588 A1	20030710	16	Fast program to program verify method	365/185.18	365/185.21; 365/189.07		Ogura, Seiki et al.						US 2003
15	✓		US 20030123308 A1	20030703		Fast program to program verify method	365/200			Ogura, Seiki et al.						
16	✓		US 20030123293 A1	20030703		Fast program to program verify method	365/185.18			Ogura, Seiki et al.						
17			US 20030123292	20030703		Fast program to program verify	365/185.18			Ogura, Seiki et al.						

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